



12V PNP POWER SWITCHING TRANSISTOR IN SOT323

Features

- BVCFO > -12V
- I_C = -1.25A Continuous Collector Current
- I_{CM} = -3A Peak Pulse Current
- Low Saturation Voltage $V_{CE(sat)} < -215 \text{mV} @ I_C = -1 \text{A}$
- $R_{CE(SAT)} = 150m\Omega$ for a Low Equivalent On-Resistance
- 500mW Power Dissipation
- Excellent hFE Characteristics up to -3A
- Complementary NPN Type: ZUMT617
- Totally Lead-Free & Fully RoHS compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

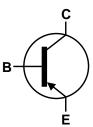
- Case: SOT323
- Case Material: Molded Plastic. "Green" Molding Compound. UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208@3
- Weight: 0.006 grams (approximate)

Applications

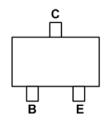
- Negative boost functions in DC-DC converters
- Supply line switching in mobile phones and pagers
- Motor drivers in camcorders and mini disk players







Device symbol



Top View Pin-Out

Ordering Information (Notes 4)

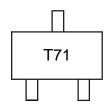
Device	Compliance	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per reel
ZUMT717TA	AEC-Q101	T71	7	8	3,000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + CI) and <1000ppm antimony compounds.

 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



T71 = Product Type Marking Code

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Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	-12	V
Collector-Emitter Voltage	V _{CEO}	-12	V
Emitter-Base Voltage	V _{EBO}	-7	V
Peak Pulse Current	I _{CM}	-3	Α
Continuous Collector Current	Ic	-1.25	Α
Base Current	I _B	-200	mA

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Power Dissipation	(Note 5)	0	385	mW	
Fower Dissipation	(Note 6)	P _D	500		
Thermal Resistance, Junction to Ambient	(Note 5)	5	325	°C/W	
Thermal Resistance, Junction to Ambient	(Note 6)	$R_{ heta JA}$	250	-C/VV	
Thermal Resistance, Junction to Leads (Note 7)		$R_{ heta JL}$	350	°C/W	
Operating and Storage Temperature Range		T _J ,T _{STG}	-55 to +150	°C	

ESD Ratings (Note 8)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

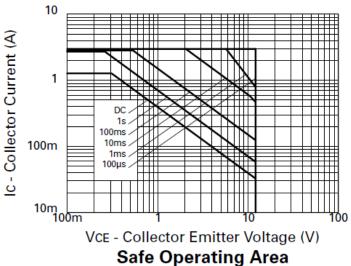
Notes:

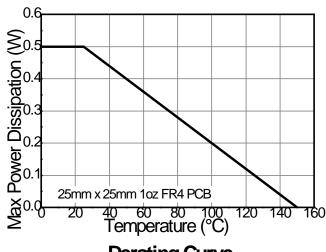
- 6. Same as note (5), except the collector lead is on a 25mm x 25mm 1oz copper.
- 7. Thermal resistance from junction to solder-point (at the end of the leads).
 8. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

^{5.} For a device mounted with collector lead on 10mm x 8mm 1oz copper that is on a single-sided 0.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.

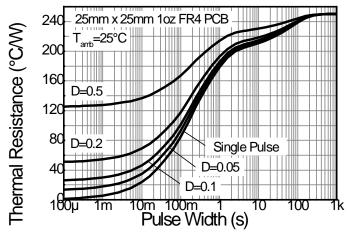


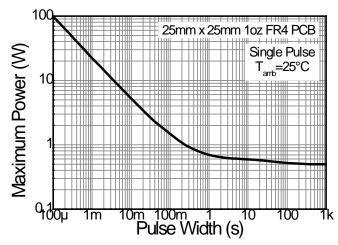
Thermal Characteristics and Derating Information











Transient Thermal Impedance

Pulse Power Dissipation

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Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 9)						
Collector-Base Breakdown Voltage	V _{CBO}	-12	_	_	V	I _C = -100μA
Collector-Emitter Breakdown Voltage	V _{CEO}	-12	_	_	V	I _C = -10mA
Emitter-Base Breakdown Voltage	V _{EBO}	-7	_	_	V	I _E = -100μA
Collector-Base Cutoff Current	I _{CBO}	_	_	-10	nA	V _{CB} = -10V
Emitter-Base Cutoff Current	I _{EBO}	_	_	-10	nA	V _{EB} = -5.6V
Collector-Emitter Cutoff Current	ICES	_	_	-10	nA	V _{CES} = -10V
ON CHARACTERISTICS (Note 9)						
		300	490			$I_C = -10 \text{mA}, V_{CE} = -2.0 \text{V}$
		300	450	-		$I_C = -0.1A$, $V_{CE} = -2.0V$
DC Current Gain		200	340			$I_C = -0.5A$, $V_{CE} = -2.0V$
Do Current Gain	hFE	125	250	_	_	$I_C = -1.25A$, $V_{CE} = -2.0V$
		75	140			$I_C = -2A$, $V_{CE} = -2.0V$
		30	80			$I_{C} = -3A$, $V_{CE} = -2.0V$
	VCE(SAT)	_	-25	-40	mV	$I_C = -0.1A, I_B = -10mA$
		_	-55	-100	mV	$I_C = -0.25A$, $I_B = -10mA$
Collector-Emitter Saturation Voltage		_	-110	-175	mV	$I_C = -0.5A$, $I_B = -10mA$
		_	-160	-215	mV	$I_C = -1A, I_B = -50mA$
			-185	-240	mV	$I_C = -1.25A$, $I_B = -100mA$
Base-Emitter Saturation Voltage	V _{BE(SAT)}		-990	-1100	mV	$I_C = -1.25A, I_B = 100mA$
Base-Emitter Turn-On Voltage	V _{BE(ON)}	_	-850	-1000	mV	$I_C = -1.25A, V_{CE} = -2.0V$
SMALL SIGNAL CHARACTERISTICS						
Output Capacitance	C _{obo}	_	15	_	pF	V _{CB} = -10V, f = 1MHz
Turn-On Time	t _(on)	_	50	_	ns	V _{CC} = -10V, I _C = -1A,
Turn-Off Time	t _(off)	_	135	_	ns	$I_{B1} = -I_{B2} = -100 \text{mA}$
Current Gain-Bandwidth Product		_	220	_	MHz	V _{CE} = -10V, I _C = -50mA, f = 100MHz

Note: 9. Measured under pulsed conditions. Pulse width ≤ 300µs. Duty cycle ≤ 2%.

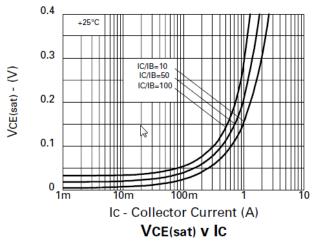
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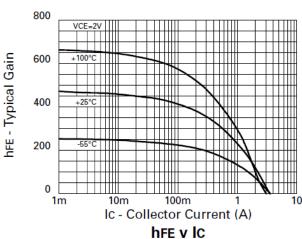
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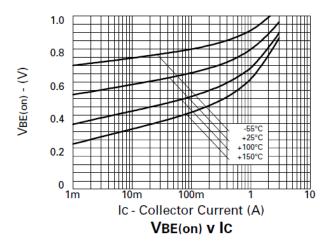
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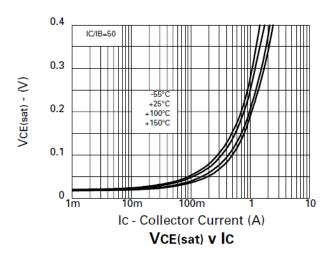


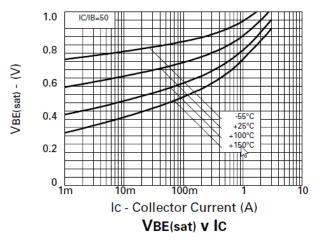
Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)







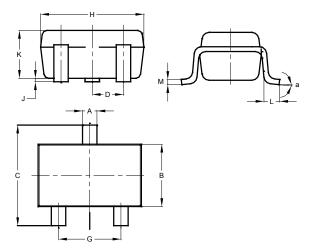






Package Outline Dimensions

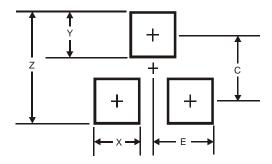
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



SOT323					
Dim	Min	Max	Тур		
Α	0.25	0.40	0.30		
В	1.15	1.35	1.30		
С	2.00	2.20	2.10		
D	0.	0.650 BSC			
F	0.375	0.475	0.425		
G	1.20	1.40	1.30		
Н	1.80	2.20	2.15		
J	0.00	0.10	0.05		
K	0.90	1.00	0.95		
L	0.25	0.40	0.30		
M	0.10	0.18	0.11		
а	8°C				
All Dimensions in mm					

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	SOT323		
Z	2.8		
Х	0.7		
Υ	0.9		
С	1.9		
E	1.0		



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